# 74HC123; 74HCT123

## Dual retriggerable monostable multivibrator with reset

Rev. 8 — 16 December 2011

**Product data sheet** 

### 1. General description

The 74HC123; 74HCT123 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC123; 74HCT123 are dual retriggerable monostable multivibrators with output pulse width control by three methods:

- 1. The basic pulse is programmed by selection of an external resistor (R<sub>EXT</sub>) and capacitor (C<sub>EXT</sub>).
- 2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input (nA) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period (nQ = HIGH, nQ = LOW) can be made as long as desired. Alternatively an output delay can be terminated at any time by a LOW-going edge on input nRD, which also inhibits the triggering.
- 3. An internal connection from nRD to the input gates makes it possible to trigger the circuit by a HIGH-going signal at input nRD as shown in the function table.

Schmitt-trigger action in the  $n\overline{A}$  and nB inputs, makes the circuit highly tolerant to slower input rise and fall times.

The 74HC123; 74HCT123 are identical to the 74HC423; 74HCT423 but can be triggered via the reset input.

#### 2. Features and benefits

- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100 % duty factor
- Direct reset terminates output pulse
- Schmitt-trigger action on all inputs except for the reset input
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from −40 °C to +85 °C and from −40 °C to +125 °C

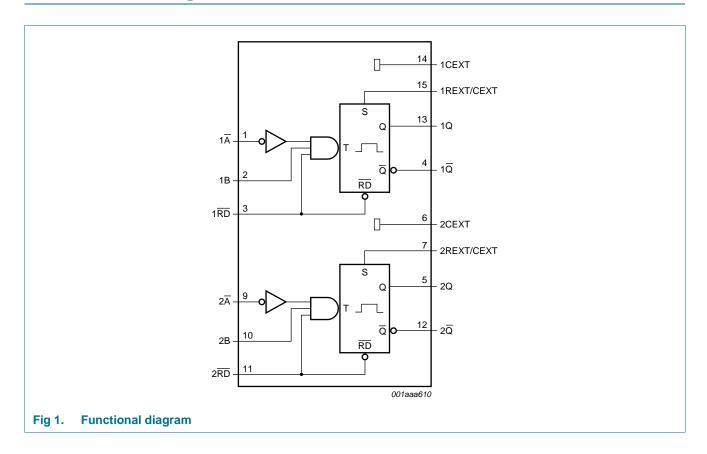


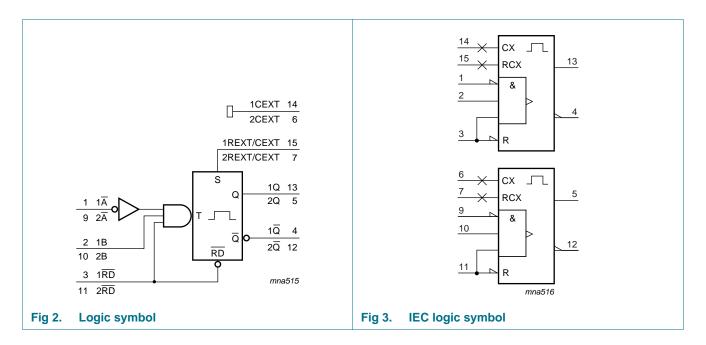
## 3. Ordering information

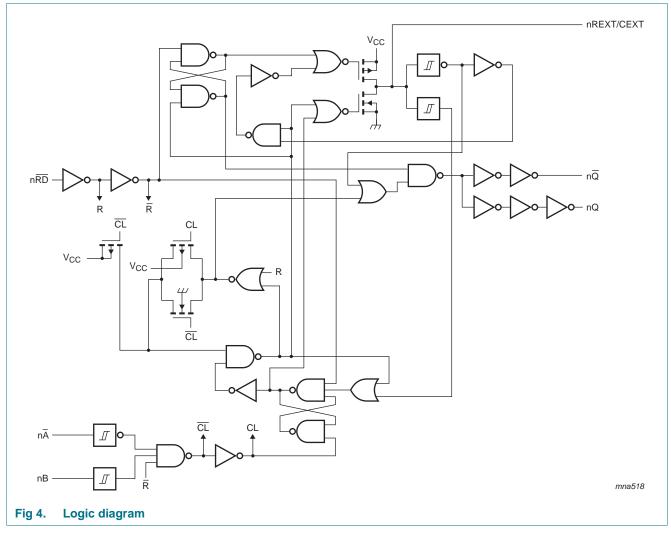
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC123N	-40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT123N				
74HC123D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1
74HCT123D			body width 3.9 mm	
74HC123DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1
74HCT123DB			body width 5.3 mm	
74HC123PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads;	SOT403-1
74HCT123PW			body width 4.4 mm	
74HC123BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5\times3.5\times0.85$ mm	SOT763-1

## 4. Functional diagram

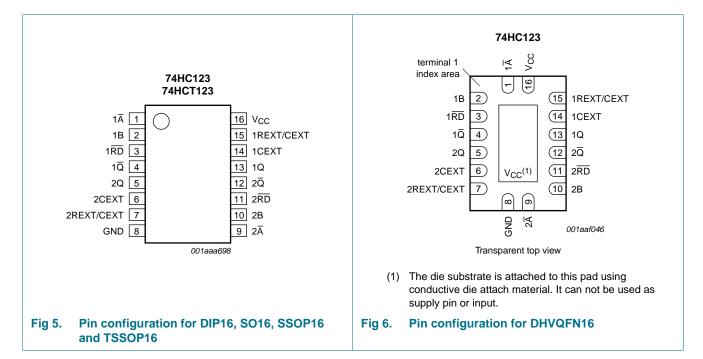






## 5. Pinning information

#### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1 <del>A</del>	1	negative-edge triggered input 1
1B	2	positive-edge triggered input 1
1RD	3	direct reset LOW and positive-edge triggered input 1
1Q	4	active LOW output 1
2Q	5	active HIGH output 2
2CEXT	6	external capacitor connection 2
2REXT/CEXT	7	external resistor and capacitor connection 2
GND	8	ground (0 V)
2Ā	9	negative-edge triggered input 2
2B	10	positive-edge triggered input 2
2RD	11	direct reset LOW and positive-edge triggered input 2
2Q	12	active LOW output 2
1Q	13	active HIGH output 1
1CEXT	14	external capacitor connection 1
1REXT/CEXT	15	external resistor and capacitor connection 1
V <sub>CC</sub>	16	supply voltage

### 6. Functional description

Table 3. Function table[1]

Input			Output		
nRD	n <del>A</del>	nB	nQ	nQ	
L	X	X	L	Н	
X	Н	X	<u>[2]</u>	H <u>[2]</u>	
X	Χ	L	<u>[2]</u>	H <u>[2]</u>	
Н	L	<b>↑</b>	Л	T	
Н	<b>\</b>	Н	Л	T	
$\uparrow$	L	Н	Л	T	

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = LOW-to-HIGH transition; ↓ = HIGH-to-LOW transition;

### 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	except for pins nREXT/CEXT; $V_O = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±25	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-	-50	mA
T <sub>stg</sub>	storage temperature		<b>−65</b>	+150	°C
P <sub>tot</sub>	total power dissipation				
	DIP16 package		<u>[1]</u> -	750	mW
	SO16 package		<u>[2]</u> -	500	mW
	SSOP16 package		<u>[3]</u> _	500	mW
	TSSOP16 package		<u>[3]</u> _	500	mW
	DHVQFN16 package		<u>[4]</u> _	500	mW

<sup>[1]</sup> For DIP16 package:  $P_{tot}$  derates linearly with 12 mW/K above 70 °C.

 $<sup>\</sup>square$  = one HIGH level output pulse;  $\square$  = one LOW level output pulse.

<sup>[2]</sup> If the monostable was triggered before this condition was established, the pulse will continue as programmed.

<sup>[2]</sup> For SO16 package:  $P_{tot}$  derates linearly with 8 mW/K above 70  $^{\circ}\text{C}.$ 

<sup>[3]</sup> For SSOP16 and TSSOP16 packages:  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C.

<sup>[4]</sup> For DHVQFN16 package: Ptot derates linearly with 4.5 mW/K above 60 °C.

## 8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	7	74HC12	3	7	4HCT12	23	Unit
			Min	Тур	Max	Min	Тур	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$\Delta t/\Delta V$	input transition rise and	nRD input							
	fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C

### 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC123	3			•			1			
$V_{IH}$	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
$V_{IL}$	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
$V_{OH}$	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μА

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	+125 °C	Uni
			Min	Тур	Max	Min	Max	Min	Max	1
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT12	23									
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μА
Δl <sub>CC</sub>	additional supply current	per input pin; $I_O = 0$ A; $V_I = V_{CC} - 2.1$ V; other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V								
		pins nĀ, nB	-	35	125	-	160	-	170	μΑ
		pin nRD	-	50	180	-	225	-	245	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

## 10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC123	3									
t <sub>pd</sub>	propagation delay	$\overline{\text{NRD}}$ , $\overline{\text{NA}}$ , $\overline{\text{NB}}$ to $\overline{\text{NQ}}$ or $\overline{\text{NQ}}$ ; $C_{\text{EXT}} = 0 \text{ pF}$ ; $R_{\text{EXT}} = 5 \text{ k}\Omega$ ;  see Figure 9	l							
		$V_{CC} = 2.0 \text{ V}$	-	83	255	-	320	-	385	ns
		$V_{CC} = 4.5 \text{ V}$	-	30	51	-	64	-	77	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	26	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	24	43	-	54	-	65	ns
		$\overline{\text{NRD}}$ (reset) to $\overline{\text{NRD}}$ (reset) to $\overline{\text{NRD}}$ (reset) to $\overline{\text{NRD}}$ ; $C_{\text{EXT}} = 0 \text{ pF}$ ; $R_{\text{EXT}} = 5 \text{ k}\Omega$ ; see Figure 9								
		V <sub>CC</sub> = 2.0 V	-	66	215	-	270	-	325	ns
		V <sub>CC</sub> = 4.5 V	-	24	43	-	54	-	65	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	20	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	19	37	-	46	-	55	ns
t <sub>t</sub>	transition time	see Figure 9	]							
		V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0 \text{ V}$	-	6	13	-	16	-	19	ns
t <sub>W</sub>	pulse width	nA LOW; see Figure 10								
		V <sub>CC</sub> = 2.0 V	100	8	-	125	-	150	-	ns
		V <sub>CC</sub> = 4.5 V	20	3	-	25	-	30	-	ns
		V <sub>CC</sub> = 6.0 V	17	2	-	21	-	26	-	ns
		nB HIGH; see Figure 10								
		V <sub>CC</sub> = 2.0 V	100	17	-	125	-	150	-	ns
		V <sub>CC</sub> = 4.5 V	20	6	-	25	-	30	-	ns
		$V_{CC} = 6.0 \text{ V}$	17	5	-	21	-	26	-	ns
		nRD LOW; see Figure 11								
		V <sub>CC</sub> = 2.0 V	100	14	-	125	-	150	-	ns
		V <sub>CC</sub> = 4.5 V	20	5	-	25	-	30	-	ns
		V <sub>CC</sub> = 6.0 V	17	4	-	21	-	26	-	ns
		nQ HIGH and n $\overline{Q}$ LOW; $V_{CC} = 5.0 \text{ V}$ ; see Figure 10 and 11	l							
		$C_{EXT}$ = 100 nF; $R_{EXT}$ = 10 k $\Omega$	-	450	-	-	-	-	-	μS
		$C_{EXT} = 0 pF;$ $R_{EXT} = 5 k\Omega$	-	75	-	-	-	-	-	ns

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50$  pF unless otherwise specified; for test circuit see <u>Figure 12</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to	+85 °C	–40 °C to	+125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
t <sub>rtrig</sub>	retrigger time	$n\overline{A}$ , nB; $C_{EXT} = 0$ pF; $R_{EXT} = 5 k\Omega$ ; $V_{CC} = 5.0$ V; see <u>Figure 10</u>	[3][4]	-	110	-	-	-	-	-	ns
R <sub>EXT</sub>	external timing	see Figure 7									
	resistor	$V_{CC} = 2.0 \text{ V}$		10	-	1000	-	-	-	-	kΩ
		$V_{CC} = 5.0 \text{ V}$		2	-	1000	-	-	-	-	kΩ
C <sub>EXT</sub>	external timing capacitor	$V_{CC} = 5.0 \text{ V}$ ; see Figure 7	<u>[4]</u>	-	-	-	-	-	-	-	pF
C <sub>PD</sub>	power dissipation capacitance	per monostable; $V_I = GND \text{ to } V_{CC}$	<u>[5]</u>	-	54	-	-	-	-	-	pF
74HCT1	23										
t <sub>PHL</sub>	HIGH to LOW propagation delay	$\overline{NRD}$ , $\overline{NA}$ , $\overline{NB}$ to $\overline{NQ}$ or $\overline{NQ}$ ; $C_{EXT} = 0$ pF; $R_{EXT} = 0$ $5 \text{ k}\Omega$ ; see Figure 9									
		$V_{CC} = 4.5 \text{ V}$		-	30	51	-	64	-	77	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	26	-	-	-	-	-	ns
		$\overline{\text{NRD}}$ (reset) to $\overline{\text{NQ}}$ or $\overline{\text{NQ}}$ ; $C_{\text{EXT}} = 0 \text{ pF}$ ; $R_{\text{EXT}} = 5 \text{ k}\Omega$ ; $\overline{\text{see}}$ Figure 9									
		$V_{CC} = 4.5 \text{ V}$		-	27	46	-	58	-	69	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	23	-	-	-	-	-	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	$\overline{ND}$ , $\overline{NA}$ , $\overline{NB}$ to $\overline{NQ}$ or $\overline{NQ}$ ; $C_{EXT} = 0$ pF; $R_{EXT} = 5$ k $\Omega$ ; see <u>Figure 9</u>									
		$V_{CC} = 4.5 \text{ V}$		-	28	51	-	64	-	77	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	26	-	-	-	-	-	ns
		$\overline{\text{NRD}}$ (reset) to $\overline{\text{NQ}}$ or $\overline{\text{NQ}}$ ; $C_{\text{EXT}} = 0$ pF; $R_{\text{EXT}} = 5$ k $\Omega$ ; see Figure 9									
		$V_{CC} = 4.5 \text{ V}$		-	23	46	-	58	-	69	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	23	-	-	-	-	-	ns
t <sub>t</sub>	transition time	V <sub>CC</sub> = 4.5 V; see <u>Figure 9</u>	<u>[1]</u>	-	7	15	-	19	-	22	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		–40 °C to	+85 °C	-40 °C to	+125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
$t_{W}$	pulse width	V <sub>CC</sub> = 4.5 V				'					•
		nA LOW; see Figure 10		20	3	-	25	-	30	-	ns
		nB HIGH; see Figure 10		20	5	-	25	-	30	-	ns
		nRD LOW; see Figure 11		20	7	-	25	-	30	-	ns
		nQ HIGH and $n\overline{Q}$ LOW; $V_{CC} = 5.0 \text{ V}$ ; see Figure 10 and 11	[2]								
		$C_{EXT}$ = 100 nF; $R_{EXT}$ = 10 k $\Omega$		-	450	-	-	-	-	-	μS
		$C_{EXT} = 0 \text{ pF};$ $R_{EXT} = 5 \text{ k}\Omega$		-	75	-	-	-	-	-	ns
t <sub>rtrig</sub>	retrigger time	$n\overline{A}$ , nB; $C_{EXT} = 0$ pF; $R_{EXT} = 5$ k $\Omega$ ; $V_{CC} = 5.0$ V; see Figure 10	[3][4]	-	110	-	-	-	-	-	ns
$R_{EXT}$	external timing resistor	$V_{CC} = 5.0 \text{ V}$ ; see Figure 7		2	-	1000	-	-	-	-	kΩ
$C_{EXT}$	external timing capacitor	$V_{CC} = 5.0 \text{ V}$ ; see <u>Figure 7</u>	[4]	-	-	-	-	-	-	-	pF
C <sub>PD</sub>	power dissipation capacitance	per monostable; $V_I = GND$ to $V_{CC}$	<u>[5]</u>	-	56	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ ;  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$
- [2] For other  $R_{EXT}$  and  $C_{EXT}$  combinations see Figure 7. If  $C_{EXT} > 10$  nF, the next formula is valid.
  - $t_W = K \times R_{EXT} \times C_{EXT}$ , where:

t<sub>W</sub> = typical output pulse width in ns;

 $R_{EXT}$  = external resistor in  $k\Omega$ ;

C<sub>EXT</sub> = external capacitor in pF;

K = constant = 0.45 for  $V_{CC} = 5.0$  V and 0.55 for  $V_{CC} = 2.0$  V.

The inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is approximately 7 pF.

[3] The time to retrigger the monostable multivibrator depends on the values of  $R_{EXT}$  and  $C_{EXT}$ . The output pulse width will only be extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time. If  $C_{EXT}$  >10 pF, the next formula (at  $V_{CC}$  = 5.0 V) for the setup time of a retrigger pulse is valid:

$$t_{rtrig} = 30 + 0.19 \times R_{EXT} \times C_{EXT}^{0.9} + 13 \times R_{EXT}^{1.05}$$
, where:

 $t_{rtrig}$  = retrigger time in ns;

 $C_{EXT}$  = external capacitor in pF;  $R_{EXT}$  = external resistor in  $k\Omega$ .

The inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

- [4] When the device is powered-up, initiate the device via a reset pulse, when  $C_{EXT} < 50$  pF.
- [5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum (C_L \times V_{CC}{}^2 \times f_o) + 0.75 \times C_{EXT} \times V_{CC}{}^2 \times f_o + D \times 16 \times V_{CC} \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_0$  = output frequency in MHz;

D = duty factor in %;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

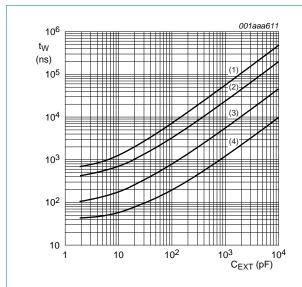
C<sub>EXT</sub> = timing capacitance in pF;

 $\sum (C_L \times V_{CC}{}^2 \times f_o)$  sum of outputs.

74HC\_HCT123

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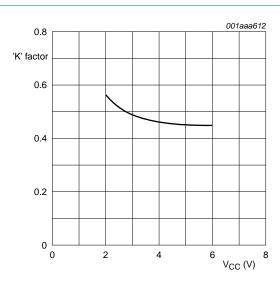
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 $V_{CC}$  = 5.0 V;  $T_{amb}$  = 25 °C.

- (1)  $R_{EXT} = 100 \text{ k}\Omega$
- (2)  $R_{EXT} = 50 \text{ k}\Omega$
- (3)  $R_{EXT} = 10 \text{ k}\Omega$
- (4)  $R_{EXT} = 2 k\Omega$

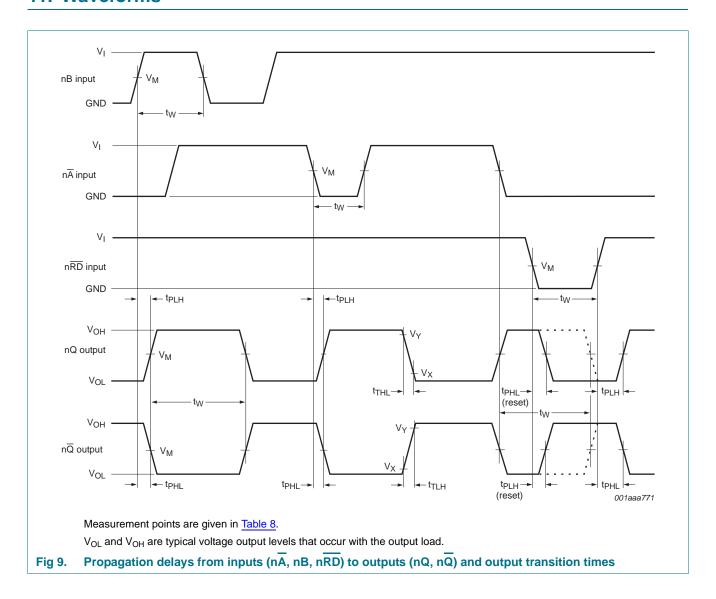
Fig 7. Typical output pulse width as a function of the external capacitor value

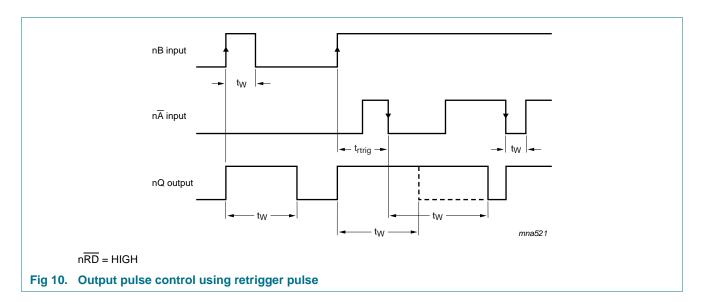


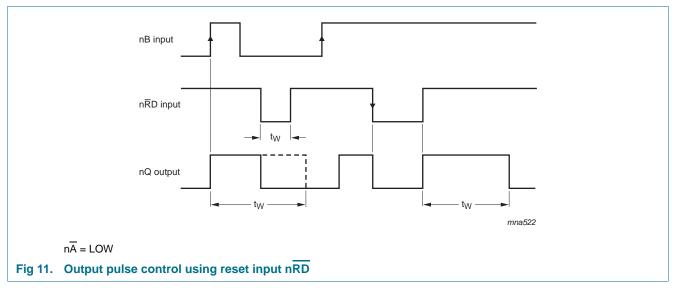
 $C_{EXT} = 10 \text{ nF; } R_{EXT} = 10 \text{ k}\Omega \text{ to } 100 \text{ k}\Omega.$   $T_{amb} = 25 \text{ °C}.$ 

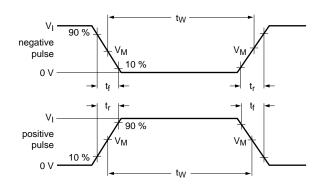
Fig 8. 74HC123 typical 'K' factor as function of V<sub>CC</sub>

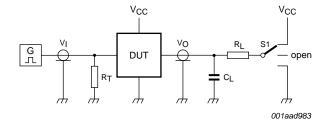
### 11. Waveforms











Test data is given in Table 8.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_L$  = Load resistance.

S1 = Test selection switch.

Fig 12. Test circuit for measuring switching times

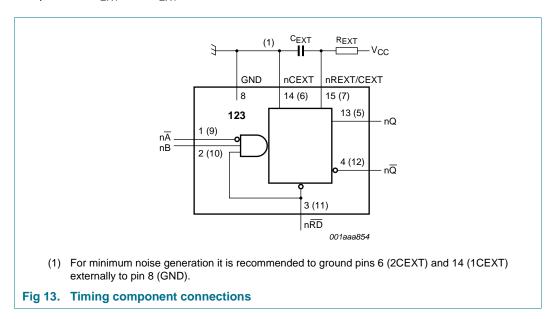
Table 8. Test data

Туре	Input	Load			S1 position
	V <sub>I</sub>	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PHL</sub> , t <sub>PLH</sub>
74HC123	V <sub>CC</sub>	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT123	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

### 12. Application information

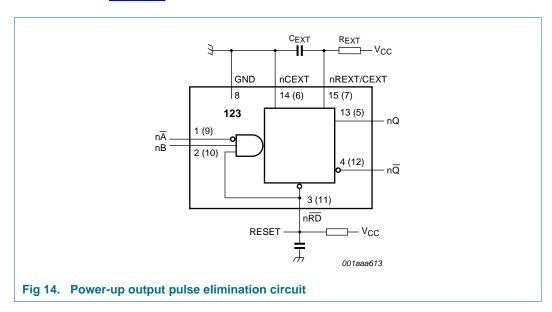
#### 12.1 Timing component connections

The basic output pulse width is essentially determined by the values of the external timing components  $R_{\text{EXT}}$  and  $C_{\text{EXT}}$ .



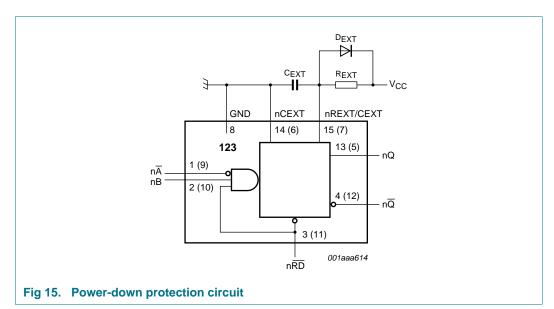
#### 12.2 Power-up considerations

When the monostable is powered-up it may produce an output pulse, with a pulse width defined by the values of  $R_{\text{EXT}}$  and  $C_{\text{EXT}}$ . This output pulse can be eliminated using the circuit shown in Figure 14.



#### 12.3 Power-down considerations

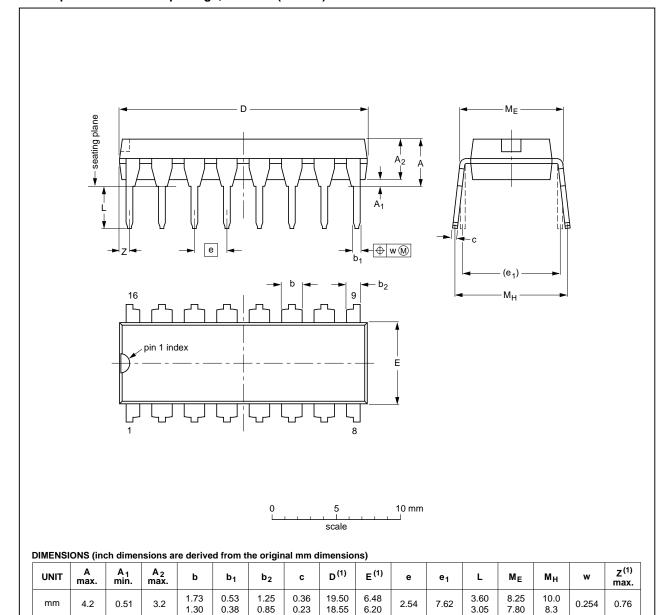
A large capacitor  $C_{EXT}$  may cause problems when powering-down the monostable due to the energy stored in this capacitor. When a system containing this device is powered-down or a rapid decrease of  $V_{CC}$  to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode ( $D_{EXT}$ ) preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in Figure 15.



### 13. Package outline

#### DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



#### Note

inches

0.17

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

0.015

0.049

0.033

0.014

0.068

0.051

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT38-4					<del>95-01-14</del> 03-02-13

0.77

0.26

0.1

0.14

0.32

Fig 16. Package outline SOT38-4 (DIP16)

0.02

0.13

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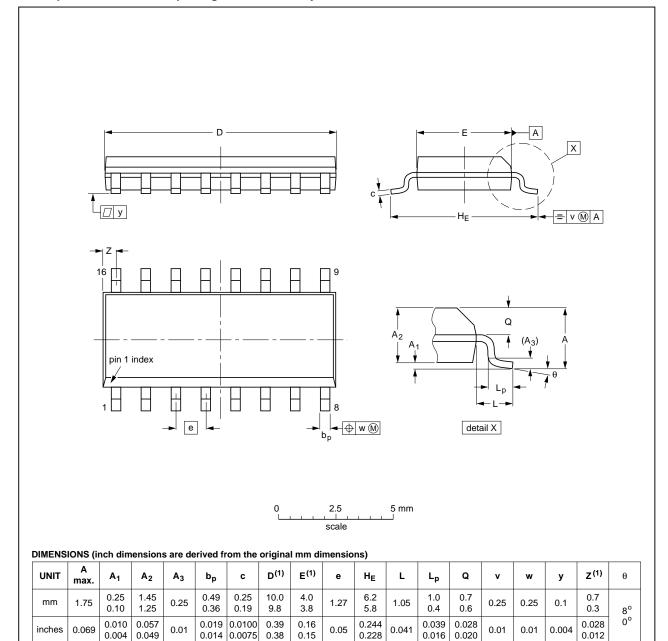
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0.01

0.03

#### SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				<del>99-12-27</del> 03-02-19	

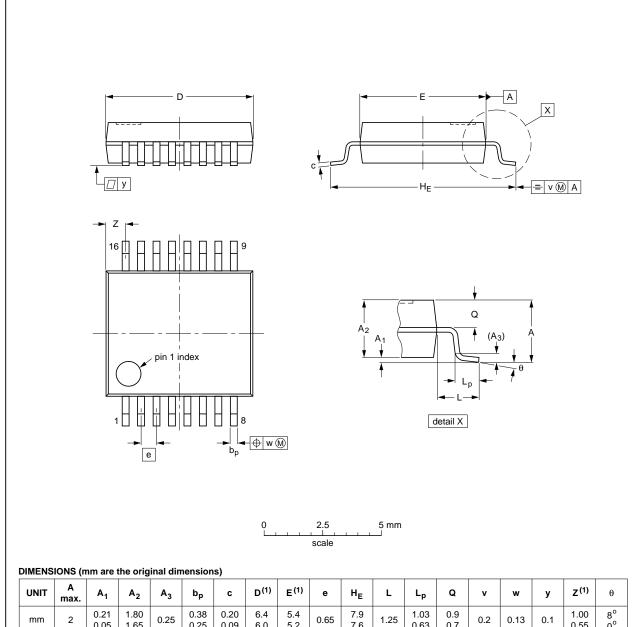
Fig 17. Package outline SOT109-1 (SO16)

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#### SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT338-1		MO-150				<del>99-12-27</del> 03-02-19

Fig 18. Package outline SOT338-1 (SSOP16)

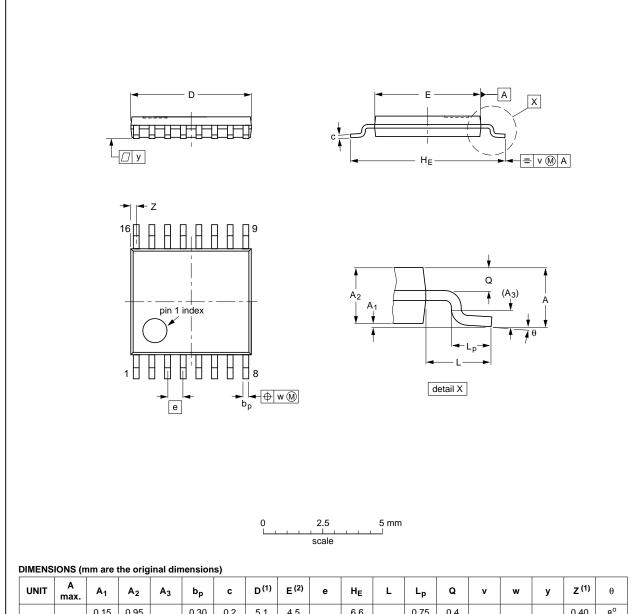
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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT403-1		MO-153				<del>99-12-27</del> 03-02-18

Fig 19. Package outline SOT403-1 (TSSOP16)

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

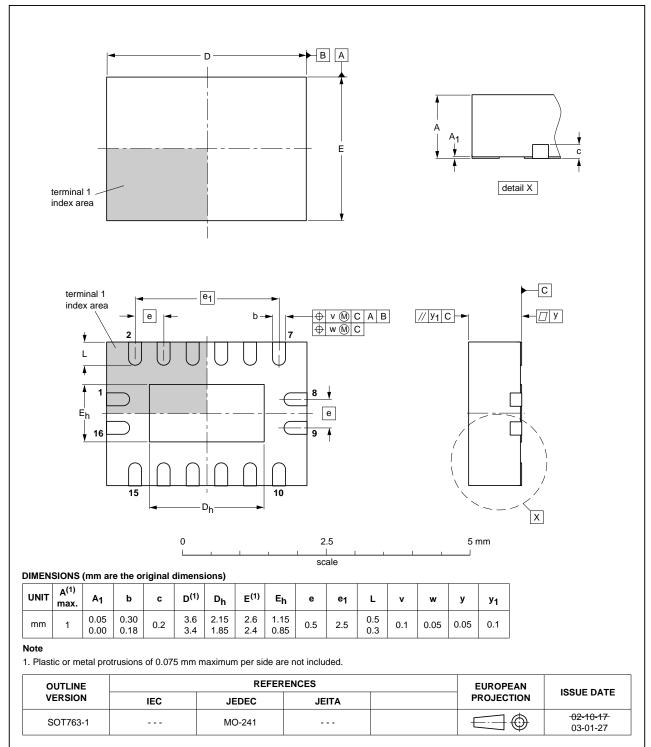


Fig 20. Package outline SOT763-1 (DHVQFN16)

74HC\_HCT123

### 14. Abbreviations

#### Table 9. Abbreviations

Acronym	Abbreviation
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

# 15. Revision history

#### Table 10. Revision history

Document ID	Release date			
Document iD	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT123 v.8	20111216	Product data sheet	-	74HC_HCT123 v.7
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
74HC_HCT123 v.7	20110825	Product data sheet	-	74HC_HCT123 v.6
74HC_HCT123 v.6	20110314	Product data sheet	-	74HC_HCT123 v.5
74HC_HCT123 v.5	20090713	Product data sheet	-	74HC_HCT123 v.4
74HC_HCT123 v.4	20060616	Product data sheet	-	74HC_HCT123 v.3
74HC_HCT123 v.3	20040511	Product specification	-	74HC_HCT123_CNV v.2
74HC_HCT123_CNV v.2	19980708	Product specification	-	-

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Dual retriggerable monostable multivibrator with reset

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